04/13/04

PTO/SB/08 (10-92)
Sheet 1 of 1.

FORM PTO-1449

INFORMATION DISCLOSURE CITATION

IN AN APPLICATION
(Use several sheets if necessary)

Docket Number (Optional)	Application Number
008226/DSM/BCVD/JW	10/824,313
Applicant(s): Zhenjiang Cui, Jun Zhao, Rick J. Roberts, Shulin Wang, Errol A. C. Sanchez, and Aihua Chen	
Filing Date: 04/13/2004	Group Art Unit: 2823

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
K.N.	5 0 0 3 1 7 8	3/26/91	Livesay	250	492.3	Nov. 14, 1988
K.N.	6 4 0 7 3 9 9	6/18/02	Livesay	250	492.3	Sep. 30, 1999

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
K.N.		S. Inaba et al. "Increase of Parasitic Resistance of Shallow p+ Extension with SiN Sidewall Process by Hydrogen Passivation of Boron and Its Improvement by Preamorphization for Sub-0.25 µm pMOSFETs" 1996 Symp. on VLSI Tech. Dig. of Technical Papers, 1996, pp. 168-169
K.N.		S. Inaba et al. "Increase of Parasitic Resistance in Shallow p+ Extension with SiN Sidewall Process and Its Improvement by Ge Preamorphization for Sub-0.25 µm pMOSFETs" IEEE Trans. Electr. Dev., Vol. 46, No. 6, June 1999, pp. 1218-1224
K.N.		M. Tanaka et al. "Realization of High Performance Dual Gate DRAMs without Boron Penetration by Application of Tetrachlorosilane Silicon Nitride Films" 2001 Symp. on VLSI Tech. Dig. of Technical Papers, 2001

EXAMINER	DATE CONSIDERED
Khuenguyen/	11/17/04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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